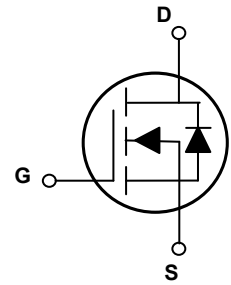
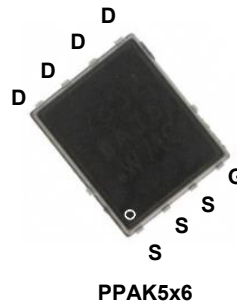


Main Product Characteristics

BV_{DSS}	60V
$R_{DS(ON)}$	2.8m Ω (Max.)
I_D	140A



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The GSGP2R806 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

Absolute Maximum Ratings ($T_J=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous, @Steady-State ($T_C=25^\circ\text{C}$)	I_D	140	A
Drain Current-Continuous, @Steady-State ($T_C=100^\circ\text{C}$)		88	
Drain Current-Pulsed ²	I_{DM}	560	A
Single Pulse Avalanche Energy ¹	E_{AS}	180	mJ
Single Pulse Avalanche Current	I_{AS}	60	A
Power Dissipation ($T_C=25^\circ\text{C}$) ³	P_D	109	W
		0.872	W/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient (PCB Mounted, Steady-State)	$R_{\theta JA}$	50	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.15	$^\circ\text{C}/\text{W}$
Operating Junction Temperature Range	T_J	-55 To +150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 To +150	$^\circ\text{C}$
Soldering Temperature	T_{SOLD}	260	$^\circ\text{C}$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On / Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V, T_J=25^\circ\text{C}$	-	-	1	μA
		$V_{DS}=60V, V_{GS}=0V, T_J=125^\circ\text{C}$	-	3	-	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=15A$	-	2.4	2.8	m Ω
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	2.2	-	3.8	V
Dynamic and Switching Characteristics						
Total Gate Charge ^{4,5}	Q_g	$V_{DD}=30V, I_D=30A, V_{GS}=10V$	-	48	-	nC
Gate-Source Charge ^{4,5}	Q_{gs}		-	17	-	
Gate-Drain ("Miller") Charge ^{4,5}	Q_{gd}		-	10	-	
Gate to Plateau ^{4,5}	$V_{plateau}$		-	5.3	-	V
Turn-On Delay Time ^{4,5}	$t_{d(on)}$	$V_{DD}=30V, R_G=4.7\Omega, V_{GS}=10V, I_D=15A$	-	20	-	nS
Rise Time ^{4,5}	t_r		-	35	-	
Turn-Off Delay Time ^{4,5}	$t_{d(off)}$		-	42	-	
Fall Time ^{4,5}	t_f		-	13	-	
Input Capacitance	C_{iss}	$V_{DS}=30V, V_{GS}=0V, F=1\text{MHz}$	-	3115	-	pF
Output Capacitance	C_{oss}		-	742	-	
Reverse Transfer Capacitance	C_{rss}		-	27	-	
Gate Resistance	R_g	$F=1\text{MHz}$	-	1.6	-	Ω
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current (Body Diode)	I_s	MOSFET symbol showing the integral reverse p-n junction diode.	-	-	140	A
Pulsed Source Current	$I_{s,pulse}$		-	-	560	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_s=30A$	-	-	1.2	V
Reverse Recovery Time ⁴	t_{rr}	$V_{GS}=0V, I_s=30A, V_R=48V, di_f/dt=100A/\mu s$	-	50	-	nS
Reverse Recovery Charge ⁴	Q_{rr}		-	76	-	nC
Reverse Recovery Peak Current ⁴	I_{rrm}		-	14	-	A

Notes:

1. $L=0.1\text{mH}, V_{DD}=48V, R_G=25\Omega$, starting temperature $T_J=25^\circ\text{C}$.
2. Pulse time of 5 μs .
3. The dissipated power value will change with the temperature. When it is greater than 25°C , the dissipated power value will decrease by 0.55°C/W for every 1 degree of temperature increase.
4. Pulse test: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
5. Basically unaffected by operating temperature.

Typical Electrical and Thermal Characteristic Curves

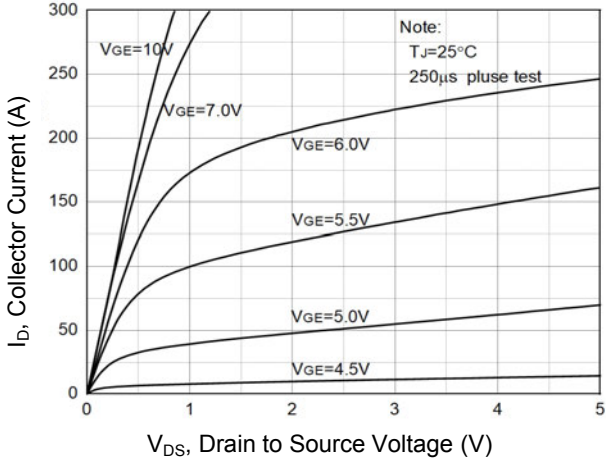


Figure 1. Typical Output Characteristics

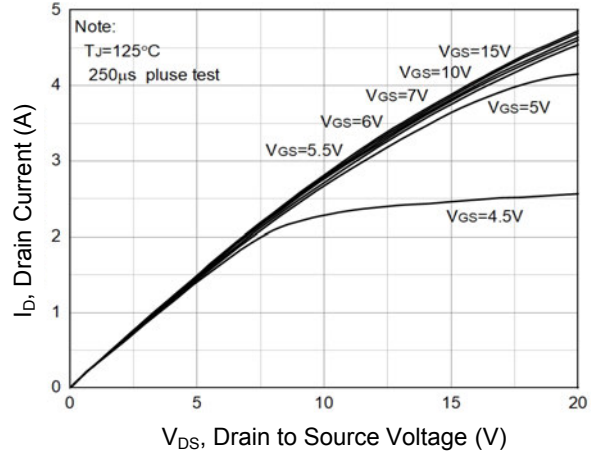


Figure 2. Typical Output Characteristics

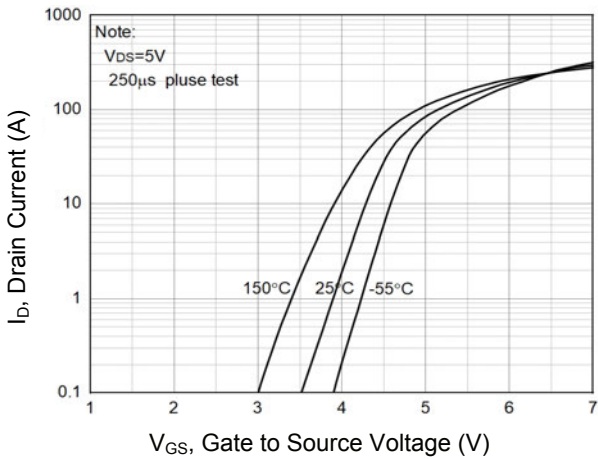


Figure 3. Transfer Characteristics

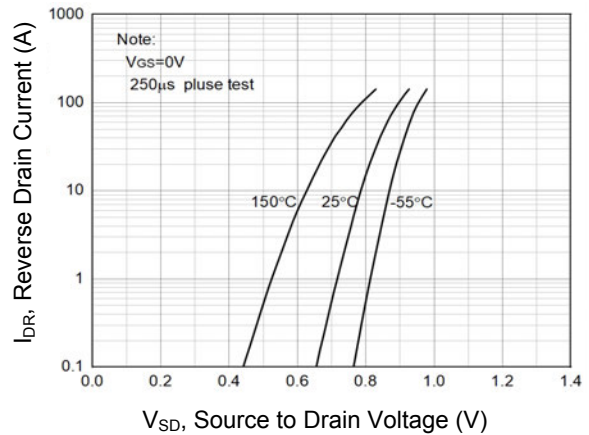


Figure 4. Body Diode Characteristics

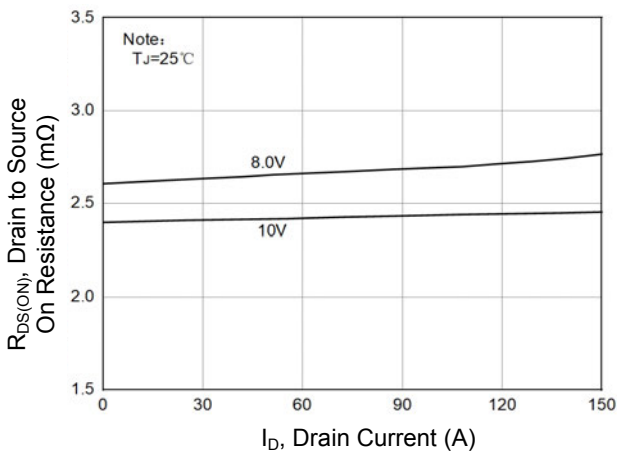


Figure 5. $R_{DS(ON)}$ vs. Drain Current

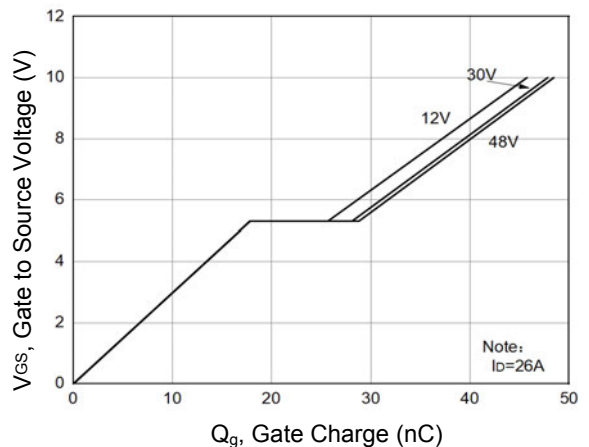


Figure 6. Gate Charge Characteristics

Typical Electrical and Thermal Characteristic Curves

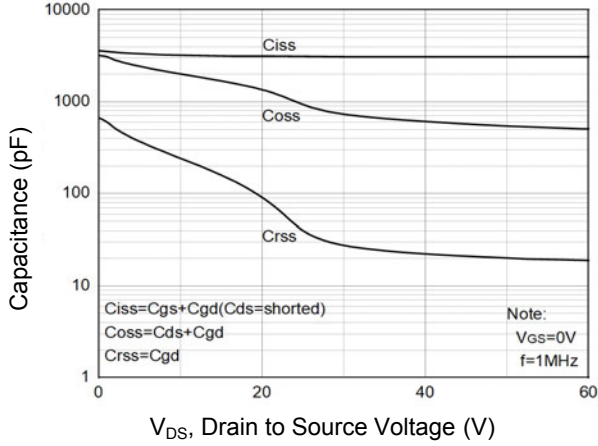


Figure 7. Capacitance Characteristics

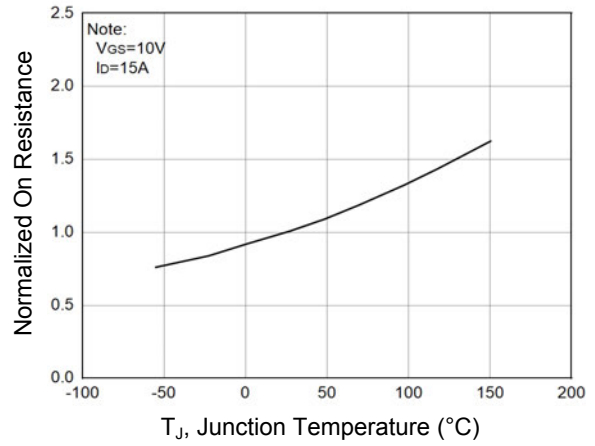


Figure 8. Normalized $R_{DS(ON)}$ vs. T_J

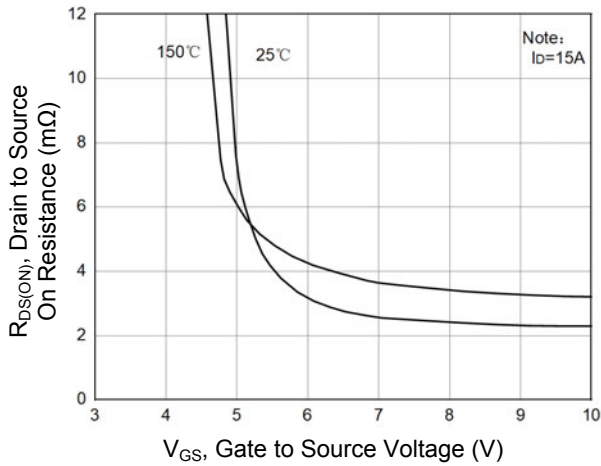


Figure 9. $R_{DS(ON)}$ vs. V_{GS}

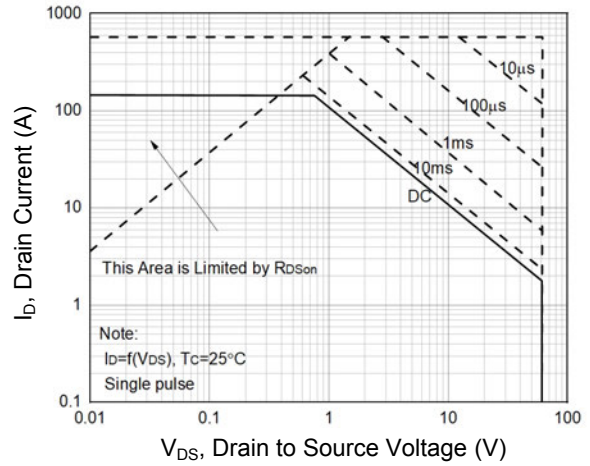


Figure 10. Maximum Safe Operation Area

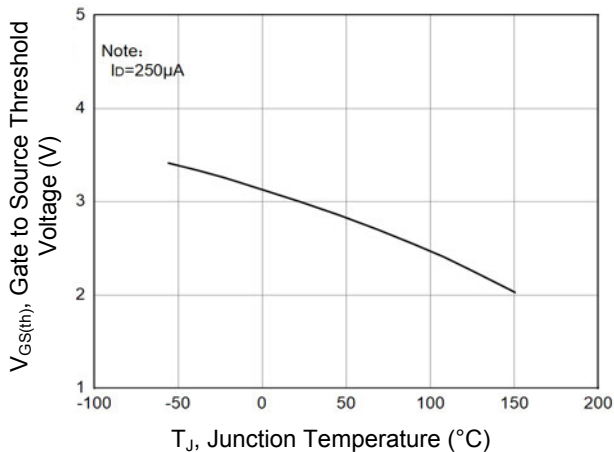


Figure 11. Gate Threshold Voltage vs. T_J

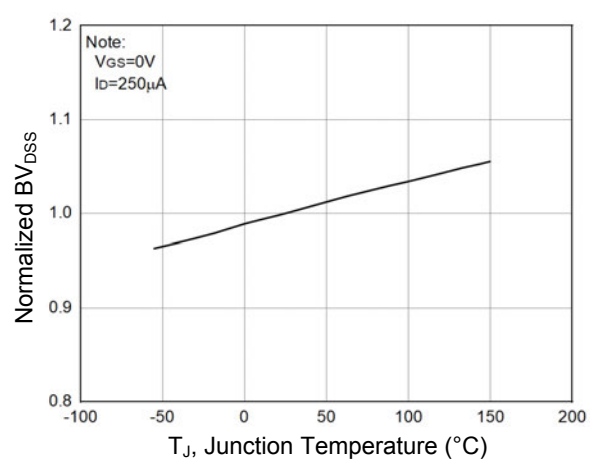


Figure 12. Normalized BV_{DS} vs. T_J

Typical Electrical and Thermal Characteristic Curves

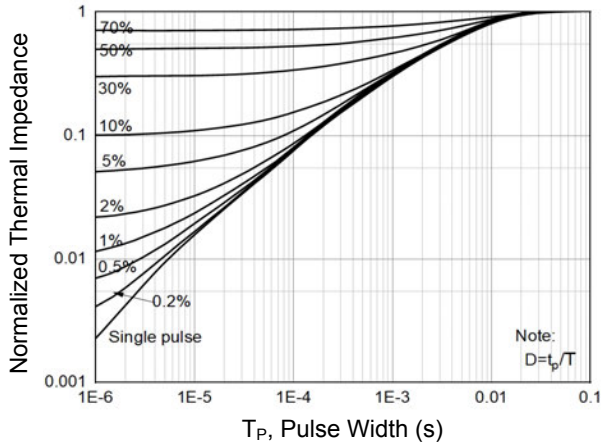


Figure 13. Transient Thermal Impedance vs. t_p

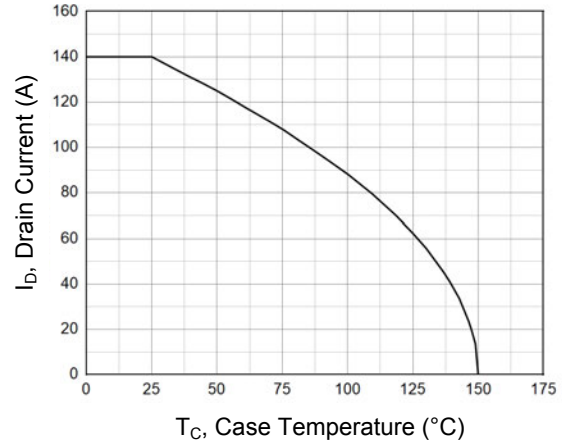
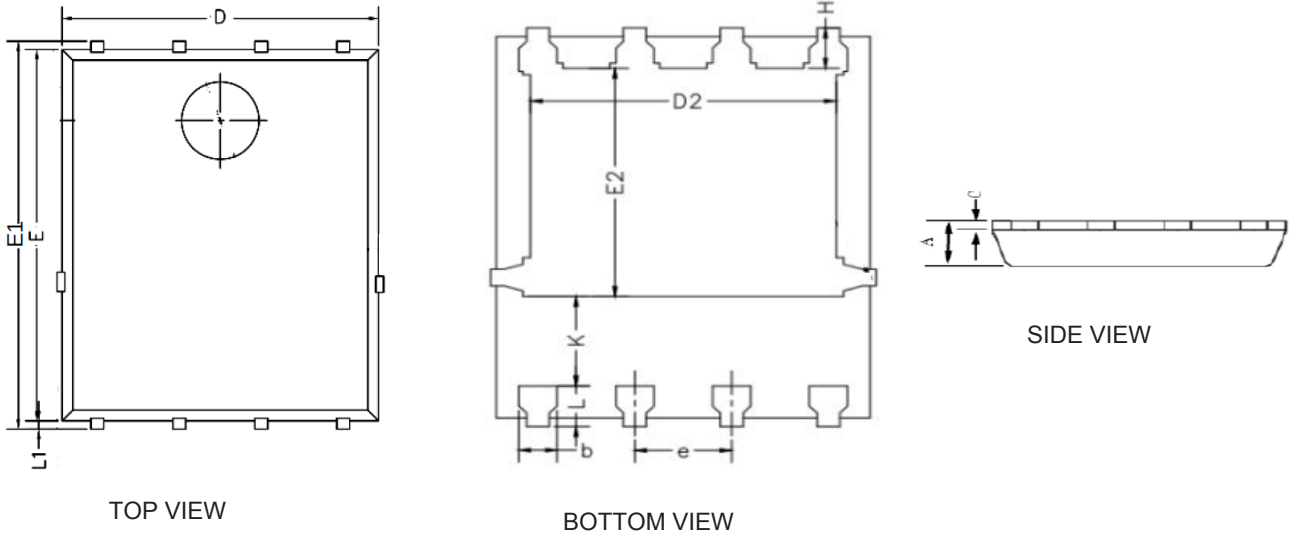


Figure 14. Power Dissipation vs. T_c

Package Outline Dimensions (PPAK5x6)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.90	1.20	0.035	0.047
b	0.30	0.55	0.012	0.022
C	0.15	0.35	0.006	0.014
D	4.70	5.20	0.185	0.205
D2	3.76	4.20	0.148	0.165
E2	3.30	3.85	0.130	0.152
E	5.60	5.90	0.220	0.232
E1	5.80	6.20	0.228	0.244
K	1.10	-	0.043	-
H	0.45	0.75	0.018	0.030
L	0.45	0.75	0.018	0.030
L1	0.25	0.45	0.010	0.018
e	1.27 BSC		0.050 BSC	

Order Information

Device	Package	Marking	Carrier	Quantity
GSGP2R806	PPAK5x6	P2R806	Tape & Reel	5,000 Pcs / Reel

For more information, please contact us at: inquiry@goodarksemi.com